

SSCN3904GS6

NPN Switching Transistor

Features

VCE	VBE	VCESAT	IC	
40V	6V	300mV	200mA	

> Description

The NPN Transistor is designed for use in linear and switching applications. The device is housed in the SOT-23 package, which is designed for telephony and professional communication equipment.

Applications

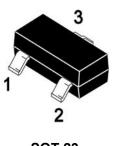
SSC-V1.0

- General purpose switching and amplification
- Telephony and professional communication equipment

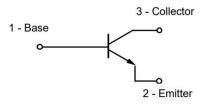
Ordering Information

Device	Package	Shipping
SSCN3904GS6	SOT-23	3000/Reel

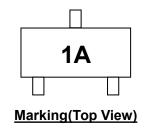
> Pin configuration



SOT-23



Circuit Diagram





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ightarrow Absolute Maximum Ratings(T_A=25°C unless otherwise noted)

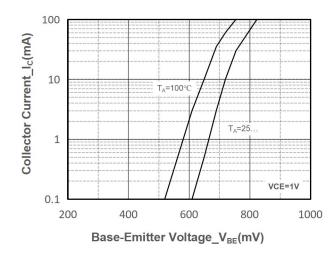
Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	60	V
Collector- Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6	V
Collector Current-Continuous	Ic	200	mA
Collector Power Dissipation	Pc	200	mW
Junction Temperature	TJ	150	$^{\circ}$
Storage Temperature	T _{STG}	-55 to 150	$^{\circ}$

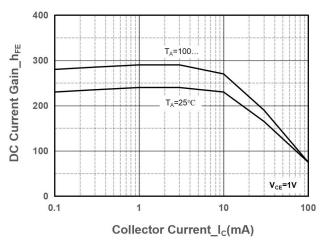
➤ Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Collector-Base Breakdown Voltage	ВУсво	I _C =10uA,I _E =0	60			V
Collector-emitter Breakdown Voltage	BV _{CEO}	I _C =1mA,I _B =0	40			V
Emitter -Base Breakdown Voltage	BV _{EBO}	I _E =10uA,I _C =0	6			V
Collector Cutoff Current	I _{CEX}	V _{CE} =30V, V _{EB} =3V			50	nA
Collector Cutoff Current	I _{CBO}	V _{CB} =30V,I _E =0			100	nA
Emitter Cutoff Current	I _{EBO}	V _{EB} =3V,I _C =0			100	nA
		V _{CE} =1V,I _C =10mA	100		300	
DC Current Gain	h _{FE}	V _{CE} =1V,I _C =0.1mA	40			
		V _{CE} =1V,I _C =100mA	30			
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =50mA,I _B =5mA			0.3	V
Base-Emitter Saturation Voltage	V _{BE(sat)}	I _C =50mA,I _B =5mA			0.95	V
Transition fraguency	f	V _{CE} =20V,I _C =10mA	250	50		MHz
Transition frequency	f⊤	f=100MHz				
Delay Time	+ .	V _{CC} =3V,V _{BE(off)} =-0.5V			35	ns
Delay Time	t _d	I _C =10mA,I _{B1} =1mA				
Rise Time	+	V _{CC} =3V,V _{BE(off)} =-0.5V			35	ns
Rise Tillie	t _r	I _C =10mA,I _{B1} =1mA				
Storage Time	t _s	V _{CC} =3V,I _C =10mA			200	ns
Storage Time		I _{B1} = I _{B2} =1mA				
Fall Time	t _f	V _{CC} =3V,I _C =10mA			50	ns
Tail Tillie		I _{B1} = I _{B2} =1mA				



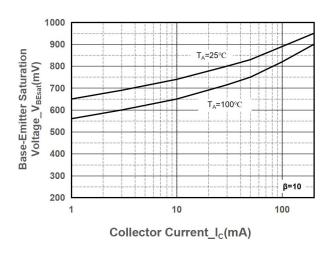
\succ Typical Performance Characteristics (T_A=25 $^{\circ}$ C unless otherwise noted)

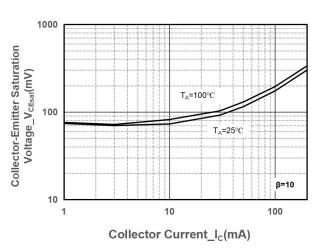




Collector Current vs. Base-Emitter Voltage

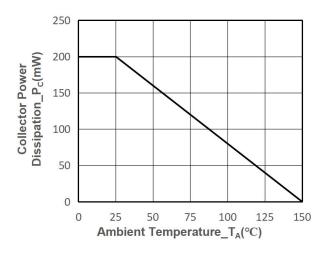
DC Current Gain vs. Collector Current

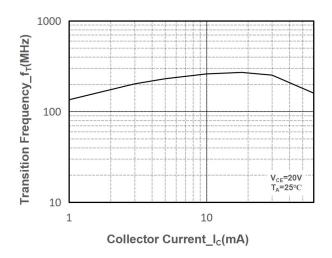




V_{BE(sat)} vs. Collector Current

V_{CE(sat)} vs. Collector Current



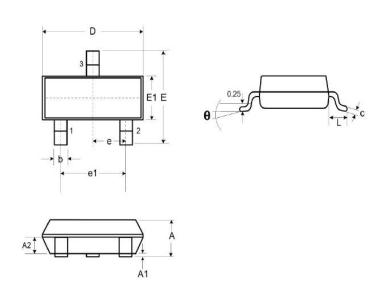


Power derating vs. Ambient temperature

Transition Frequency vs. Collector Current

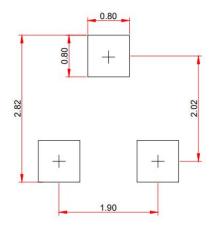


> Package Information



DIM	Millimeters			
	Min.	Тур.	Max.	
Α	0.89	-	1.12	
A 1	0.01	1	0.10	
A2	0.88	0.95	1.02	
b	0.30	-	0.51	
С	0.08	1	0.18	
D	2.80	2.90	3.04	
E	2.10	2.37	2.64	
E1	1.20	1.30	1.40	
е		0.95		
e1		1.90		
L	0.40	0.50	0.60	
L1	0.55			
N		3		
θ	0°	-	8°	

Recommended Pad outline(Unit: mm)





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